

ATTACHMENT B
Amendments to the Claims

Please cancel claims 3 and 4 without prejudice or disclaimer.

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently amended) An etching solution comprising:

(i) hydrofluoric acid;

(ii) water in a concentration of 30% by weight or lower; and

(iii) at least one member selected from the group consisting of an organic acid, an inorganic acid and an organic solvent having a hetero atom, whose content ranges from 30 to 99.9% by weight,

wherein the etching solution has a ratio of an etch rate of a boron silicate glass film (BSG) or boron phosphosilicate glass / an etch rate of a thermal oxide film (THOX) at 25°C is of 20 or higher.

2. (Currently Amended) The etching solution according to claim 1, wherein-a

the organic solvent in the etching solution has a relative dielectric constant of 61 or lower.

3. (Cancel)

4. (Cancel)

5. (Currently Amended) The etching solution according to claim 1, wherein
the weight the organic solvent is isopropyl alcohol and the etching solution has a
constituent ratio of HF : isopropyl alcohol : water is by 0.1-50% by weight : 30-99% by
weight : 0-70% by weight.

6. (Currently Amended) The etching solution according to claim 1, wherein
the weight the organic acid is acetic acid and the etching solution has a constituent ratio
of HF : acetic acid : water is 0.1-50% by weight : 30-99.9% by weight : 0-70% by weight.

7. (Currently Amended) The etching solution according to claim 1, wherein
the weight the organic solvent comprises tetrahydrofuran and the etching solution has a
constituent ratio of HF : tetrahydrofuran : water is 0.1-50% by weight : 30-99.9% by
weight : 0-70% by weight.

8. (Currently Amended) The etching solution according to claim 1, wherein
the weight the organic solvent is acetone and the etching solution has a constituent ratio
of HF : acetone : water is 0.1-50% by weight : 30-99.9% by weight : 0-70% by weight.

9. (Currently Amended) The etching solution according to claim 1, wherein
the weight the organic solvent comprises methanol and the etching solution has a
constituent ratio of HF : methanol : water is 0.1-50% by weight : 30-99.9% by weight :
0-70% by weight.

10. (Currently Amended) The etching solution according to claim 1, wherein the weight the organic solvent comprises ethanol and the etching solution has a constituent ratio of HF : ethanol : water is 0.1-50% by weight : 30-99.9% by weight : 0-70% by weight.

11. (Currently Amended) The etching solution according to claim 1, the solution comprising wherein the solution comprises an inorganic acid.

12. (Original) The etching solution according to claim 11, wherein the inorganic acid has a pKa value at 25°C of 2 or lower.

13. (Currently Amended) The etching solution according to claim 11, wherein the weight the inorganic acid is HCl and the etching solution has a constituent ratio of HF : HCl : water is 0.01-50% by weight : 1-36% by weight : 0-99% by weight.

14. (Currently Amended) The etching solution according to claim 11, wherein the weight the inorganic acid is HNO₃ and the etching solution has a constituent ratio of HF : HNO₃ : water is 0.01-50% by weight : 1-70% by weight : 0-99% by weight.

15. (Previously Presented) A method for producing an etched article by etching an article to be etched with the etching solution as defined in claim 1.

16. (Original) An etched article which is obtainable by the method of claim 15.